

FORM PTO-1449  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (Use several sheets if necessary)  JUN 21 2004	<b>Docket Number (Optional)</b> 81912.0009	<b>Application Number</b> 10/806,681
	<b>Applicant</b> SUGAWARA, et al.	
	<b>Filing Date</b> March 23, 2004	<b>Group Art Unit</b> 2811

## U.S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

AICS	IWAYA, et al., "Reduction of Etch Pit Density in Organometallic Vapor Phase Exptaxy-Grown GaN on Sapphire by Insertion of a Low-Temperature-Deposited Buffer Layer between High-Temperature-Grown GaN" Jpn.J. Appl. Phys. Vol. 37 (1998) pp. 316-318
AICS	AMANO, et al., "Stress and Defect Control in GaN Using Low Temperature Interlayers" Jpn.J. Appl. Phys. Vol. 37 (1998) pp. 1540-1542)

EXAMINER <i>Asst. William S. Schara</i>	DATE CONSIDERED <i>12/19/05</i>
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.	